

Ultra-Low Offset Voltage Operational Amplifier

OP07

1.0 SCOPE

This specification documents the detailed requirements for Analog Devices space qualified die including die qualification as described for Class K in MIL-PRF-38534, Appendix C, Table C-II except as modified herein.

The manufacturing flow described in the STANDARD DIE PRODUCTS PROGRAM brochure at http://www.analog.com/marketSolutions/militaryAerospace/pdf/Die_Broc.pdf is to be considered a part of this specification.

This data sheet specifically details the space grade version of this product. A more detailed operational description and a complete data sheet for commercial product grades can be found at www.analog.com/OP07

2.0 Part Number. The complete part number(s) of this specification follow:

Part Number Description

OP07-000C Ultra-Low Offset Voltage Operational Amplifier

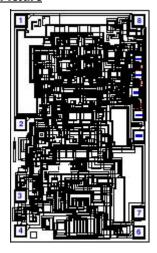
OP07R000C Radiation Tested Ultra-Low Offset Voltage Operational Amplifier

3.0 <u>Die Information</u>

3.1 <u>Die Dimensions</u>

Die Size	Die Thickness	Bond Pad Metalization
57 mil x 93 mil	19 mil ± 2 mil	Al/Cu

3.2 <u>Die Picture</u>



- 1. V_{IO} TRIM
- 2. -INPUT
- 3. +INPUT
- $4. -V_S$
- 5. NC
- 6. OUTPUT
- 7. $+V_S$
- 8. V_{IO} TRIM

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3.3 Absolute Maximum Ratings 1/

Supply Voltage (V _S)	±22V dc
Input Voltage (V _{IN}) <u>2/</u>	±22V dc
Differential Input Voltage	±30V dc
Output Short Circuit Duration	Indefinite
Storage Temperature Range	65°C to +150°C
Junction Temperature	+150°C
Ambient Operating Temperature Range	55°C to +125°C

Absolute Maximum Ratings Notes:

4.0 <u>Die Qualification</u>

In accordance with class-K version of MIL-PRF-38534, Appendix C, Table C-II, except as modified herein

- (a) Qual Samples Size and Qual Acceptance Criteria 10/0
- (b) Qual Sample Package DIP
- (c) Pre-screen electrical test over temperature performed post-assembly prior to die qualification.

Table I - Dice Electrical Characteristics								
Parameter	Symbol Conditions <u>1/</u>		Limit Min	Limit Max	Units			
Input Offset Voltage	V _{IO}		-25	+25	μV			
lanut Diag Compant	+I _{IB}		-2	+2	nA			
Input Bias Current	-I _{IB}		-2	+2				
Input Offset Current	l _{IO}		-2	+2	nA			
Power Supply Rejection Ratio	PSRR	$V_S = \pm 3V \text{ to } \pm 18V$	-10	10	μV/V			
Input Voltage Range	IVR		±13		V			
Common Mode Rejection Ratio	CMRR	$V_{CM} = IVR$	110		dB			
Supply Current	Is	No Load		4	mA			
O to Welfers C :	, , , , , , , , , , , , , , , , , , ,	$R_L = 1k\Omega$	±10		.,			
Output Voltage Swing	put Voltage Swing V_{OP} $R_L = 2k \Omega$		±12		V			
Open Loop Voltage Gain	Avs	$V_{OUT} = \pm 10V$, $R_L = 2k\Omega$	300		V/m\			
Slew Rate	+SR, -SR	$V_{IN} = \pm 5V$, $A_{VS} = 1$	0.08		V/µs			

Table I Notes:

 $1/V_S = \pm 15V$, $V_{CM} = 0V$, and $T_A = 25$ °C, unless otherwise specified.

^{1/} Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

 $[\]underline{2}$ / For supply voltage less than ± 22 V, the absolute maximum input voltage is equal to the supply voltage.

Table II - Electrical Characteristics for Qual Samples								
Parameter	Symbol	Conditions <u>1/</u>		Sub- groups	Limit Min	Limit Max	Units	
				1	-25	25		
Input Offset Voltage	V _{IO}			2, 3	-60	60	μV	
			M, D, L. R <u>3</u> /	1	-400	400		
		V _{CM} =	- 0\/	1	-2	2		
Input Offset Current	lio	VCM-	- UV	2, 3	-4	4	nA	
			M, D, L. R <u>3</u> /	1	-25	25		
				1		4		
Supply Current <u>2</u> /	ls			2, 3		5	mA	
			M, D, L. R <u>3</u> /	1		4		
Input Offset Voltage Temperature Sensitivity <u>2</u> /	ΔVIO/Δt			2, 3	-0.6	0.6	μV/°C	
Input Voltage Range <u>2</u> /	IVR			1, 2, 3	-13	13	V	
Dower Supply Dejection Datio 2/	PSRR	Vc - +2V	Vs = ±3V to ±18V		-10	10		
Power Supply Rejection Ratio <u>2</u> /	PORK	V2 = ∓2V	10 ±16V	2, 3	-20	20	μV/V	
Input Offset Adjustment Range <u>2</u> /	+VIO ADJ			1	0.5			
input Onset Aujustinent hänge <u>2</u> /	-VIOADJ			'		-0.5	mV	
		RL=	1kΩ	1, 2, 3	-10	10		
Output Voltage Swing <u>2</u> /	V _{OP}	RL=	$R_L = 2k\Omega$		-12	12	- V	
		Vout = ± 10 V, R _L = 2 k Ω		1	300			
Open Loop Voltage Gain	A vs			2, 3	200		V/mV	
			M, D, L. R <u>3</u> /	1	100			
Common Mode Rejection Ratio <u>2</u> /	Delication Paris 2/ CMPP V 11/2		- IVR	1	110		dB	
Common Mode Rejection ratio <u>2</u> /	CMRR	V _{CM} = IVR		2, 3	106		UB	
Slew Rate <u>2</u> /	±SR	VIN = ±5\	/, AV = 1	4	0.08		V/µS	

Table III - Life Test Endpoint and Delta Parameter
(Product is tested in accordance with Table II with the following exceptions)

		Sub-	Post Burn In Limit		Post Life Test Limit		Life	
Parameter	Symbol	groups	Min	Max	Min	Max	Test Delta	Units
Input Offset Voltage	V _{IO}	4	-60	60	-135	135	±75	
		5, 6			-170	170		μ۷
Input Bias Current	+l _{IB}	1	-3	+3	-4	+4	±1	
		2, 3			-6	+6		A
		1	-3	+3	-4	+4	±1	nA
		2, 3			-6	+6		
Input Offset Current	lio	1	-3	+3	-4	+4		A
		2, 3			-6	+6		nA

Life Test/Burn-In Information 5.0

- 5.1 HTRB is not applicable for this drawing.
- Burn-in is per MIL-STD-883 Method 1015 test condition B or C. Steady state life test is per MIL-STD-883 Method 1005. 5.2
- 5.3

Rev	Description of Change	Date
Α	Initiate	2 Nov. 2001
В	Change PSRR range from ± 4.5 to ± 20 V to ± 3 to ± 18 V on Table I. Update web address	20 Dec. 2001
С	Add radiation part. Update web address	Feb. 10, 2003
D	Die picture labeled incorrectly, update to current revision.	July 22, 2003
Е	Update 1.0 Scope description.	23 Jul. 2007
F	Update header/footer & add to 1.0 scope description.	Feb. 13,2008
G	Add Junction Temperature+150°C to 3.3 Absolute Max. Ratings	March 31, 2008
Н	Updated Section 4.0c note to indicate pre-screen temp testing being performed.	June 5, 2009
I	Updated fonts and sizes to ADI standards	Sept 27, 2011